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# **Dual Bias Resistor Transistors**

# NPN and PNP Silicon Surface Mount Transistors with Monolithic Bias Resistor Network

The BRT (Bias Resistor Transistor) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base–emitter resistor. These digital transistors are designed to replace a single device and its external resistor bias network. The BRT eliminates these individual components by integrating them into a single device. In the EMD5DXV6 series, two complementary BRT devices are housed in the SOT–563 package which is ideal for low power surface mount applications where board space is at a premium.

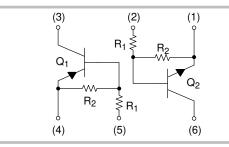
#### **Features**

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- Available in 8 mm, 7 inch Tape and Reel
- Lead Free Solder Plating
- These Devices are Pb-Free and are RoHS Compliant



# ON Semiconductor®

http://onsemi.com





SOT-563 CASE 463A

#### **MARKING DIAGRAM**



U5 = Specific Device Code

M = Month Code

= Pb-Free Package

(Note: Microdot may be in either location)

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
EMD5DXV6T5G	SOT-563 (Pb-Free)	8000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

 $\textbf{MAXIMUM RATINGS} \ (T_A = 25^{\circ}C \ unless \ otherwise \ noted, common \ for \ Q_1 \ and \ Q_2, - \ minus \ sign \ for \ Q_1 \ (PNP) \ omitted)$ 

Rating	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	50	Vdc
Collector-Emitter Voltage	$V_{CEO}$	50	Vdc
Collector Current	I <sub>C</sub>	100	mAdc

# THERMAL CHARACTERISTICS

	Symbol	Max	Unit	
Total Device Dissipation  Derate above 25°C	T <sub>A</sub> = 25°C	P <sub>D</sub>	357 (Note 1) 2.9 (Note 1)	mW mW/°C
Thermal Resistance	Junction-to-Ambient	$R_{ heta JA}$	350 (Note 1)	°C/W
	Symbol	Max	Unit	
Total Device Dissipation  Derate above 25°C	T <sub>A</sub> = 25°C	PD	500 (Note 1) 4.0 (Note 1)	mW mW/°C
Thermal Resistance	Junction-to-Ambient	$R_{ heta JA}$	250 (Note 1)	°C/W
Junction and Storage Temperature			-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

<sup>1.</sup> FR-4 @ Minimum Pad

#### **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Resistor Ratio

Characteristic	Symbol	Min	Тур	Max	Unit
Q1 TRANSISTOR: PNP					
OFF CHARACTERISTICS					
Collector-Base Cutoff Current (V <sub>CB</sub> = 50 V, I <sub>E</sub> = 0)	I <sub>CBO</sub>	_	-	100	nAdc
Collector-Emitter Cutoff Current (V <sub>CB</sub> = 50 V, I <sub>B</sub> = 0)	I <sub>CEO</sub>	-	-	500	nAdc
Emitter-Base Cutoff Current (V <sub>EB</sub> = 6.0, I <sub>C</sub> = 5.0 mA)	I <sub>EBO</sub>	_	-	1.0	mAdc
ON CHARACTERISTICS					
Collector-Base Breakdown Voltage ( $I_C = 10 \mu A, I_E = 0$ )	V <sub>(BR)CBO</sub>	50	-	_	Vdc
Collector-Emitter Breakdown Voltage (I <sub>C</sub> = 2.0 mA, I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub>	50	-	_	Vdc
DC Current Gain (V <sub>CE</sub> = 10 V, I <sub>C</sub> = 5.0 mA)	h <sub>FE</sub>	20	35	_	
Collector-Emitter Saturation Voltage (I <sub>C</sub> = 10 mA, I <sub>B</sub> = 0.3 mA)	V <sub>CE(SAT)</sub>	-	-	0.25	Vdc
Output Voltage (on) (V <sub>CC</sub> = 5.0 V, V <sub>B</sub> = 2.5 V, R <sub>L</sub> = 1.0 k $\Omega$ )	V <sub>OL</sub>	-	-	0.2	Vdc
Output Voltage (off) (V <sub>CC</sub> = 5.0 V, V <sub>B</sub> = 0.5 V, R <sub>L</sub> = 1.0 k $\Omega$ )	V <sub>OH</sub>	4.9	-	_	Vdc
Input Resistor	R1	3.3	4.7	6.1	kΩ
Resistor Ratio	R1/R2	0.38	0.47	0.56	
Q2 TRANSISTOR: NPN					
OFF CHARACTERISTICS					
Collector-Base Cutoff Current ( $V_{CB} = 50 \text{ V}, I_{E} = 0$ )	I <sub>CBO</sub>	_	-	100	nAdc
Collector-Emitter Cutoff Current (V <sub>CB</sub> = 50 V, I <sub>B</sub> = 0)	I <sub>CEO</sub>	-	-	500	nAdc
Emitter-Base Cutoff Current (V <sub>EB</sub> = 6.0, I <sub>C</sub> = 5.0 mA)	I <sub>EBO</sub>	-	-	0.1	mAdc
ON CHARACTERISTICS					
Collector-Base Breakdown Voltage ( $I_C = 10 \mu A, I_E = 0$ )	V <sub>(BR)CBO</sub>	50	-	_	Vdc
Collector-Emitter Breakdown Voltage (I <sub>C</sub> = 2.0 mA, I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub>	50	-	_	Vdc
DC Current Gain (V <sub>CE</sub> = 10 V, I <sub>C</sub> = 5.0 mA)	h <sub>FE</sub>	80	140	-	
Collector–Emitter Saturation Voltage ( $I_C = 10 \text{ mA}, I_B = 0.3 \text{ mA}$ )	V <sub>CE(SAT)</sub>	-	-	0.25	Vdc
Output Voltage (on) (V <sub>CC</sub> = 5.0 V, V <sub>B</sub> = 2.5 V, R <sub>L</sub> = 1.0 k $\Omega$ )	V <sub>OL</sub>	-	-	0.2	Vdc
Output Voltage (off) (V <sub>CC</sub> = 5.0 V, V <sub>B</sub> = 0.5 V, R <sub>L</sub> = 1.0 k $\Omega$ )	V <sub>OH</sub>	4.9	-	-	Vdc
Input Resistor	R1	33	47	61	kΩ

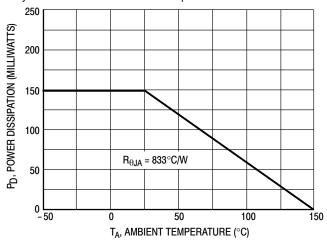
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

R1/R2

8.0

1.0

1.2



# TYPICAL ELECTRICAL CHARACTERISTICS — EMD5DXV6 PNP TRANSISTOR

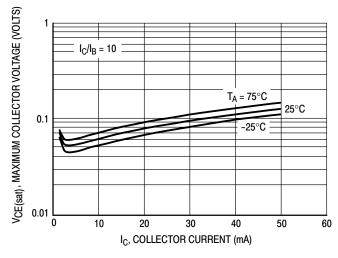


Figure 2. V<sub>CE(sat)</sub> versus I<sub>C</sub>

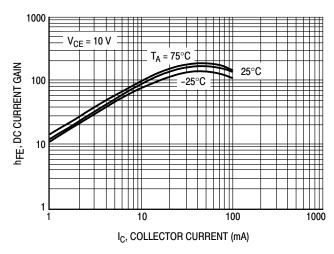


Figure 3. DC Current Gain

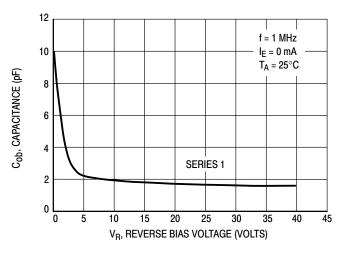


Figure 4. Output Capacitance

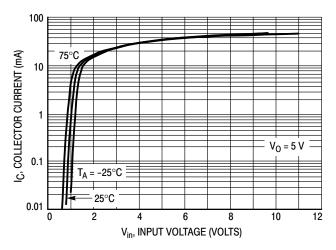


Figure 5. Output Current versus Input Voltage

# TYPICAL ELECTRICAL CHARACTERISTICS — EMD5DXV6 NPN TRANSISTOR

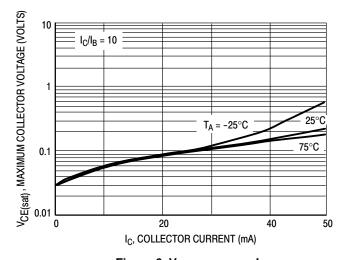


Figure 6.  $V_{CE(sat)}$  versus  $I_C$ 

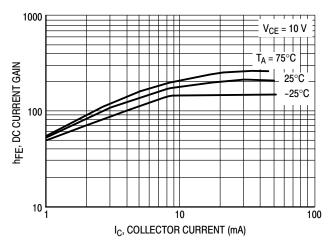


Figure 7. DC Current Gain

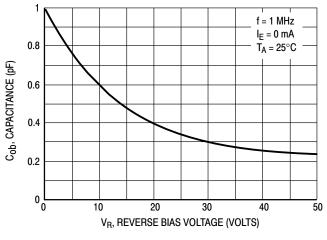


Figure 8. Output Capacitance

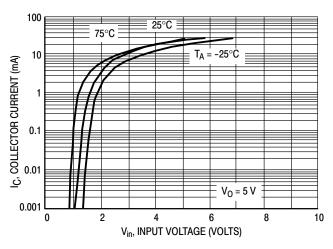


Figure 9. Output Current versus Input Voltage

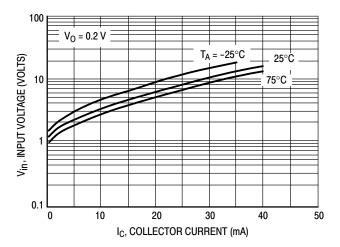
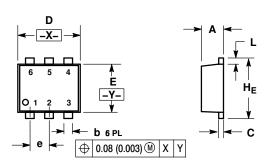


Figure 10. Input Voltage versus Output Current

#### PACKAGE DIMENSIONS

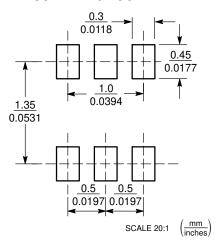
#### SOT-563, 6 LEAD CASE 463A ISSUE F



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI
  - Y14.5M, 1982.
    CONTROLLING DIMENSION: MILLIMETERS
  - MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.50	0.55	0.60	0.020	0.021	0.023
b	0.17	0.22	0.27	0.007	0.009	0.011
С	0.08	0.12	0.18	0.003	0.005	0.007
D	1.50	1.60	1.70	0.059	0.062	0.066
E	1.10	1.20	1.30	0.043	0.047	0.051
е	0.5 BSC			0.02 BSC		
Ĺ	0.10	0.20	0.30	0.004	0.008	0.012
HE	1.50	1.60	1.70	0.059	0.062	0.066

#### **SOLDERING FOOTPRINT**



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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